



#### 60V NPN MEDIUM POWER TRANSISTOR IN SOT223

#### Mechanical Data

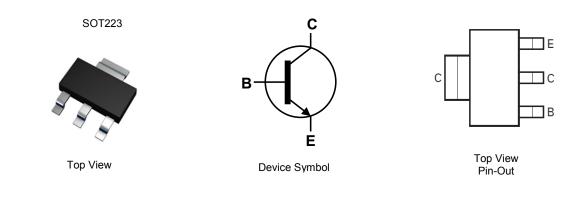
• BV<sub>CEO</sub> > 60V

**Features** 

- I<sub>C</sub> = 6A High Continuous Collector Current
- I<sub>CM</sub> = 20A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < 100mV @ 1A</li>
- $R_{CE(sat)} = 44m\Omega$  for a Low Equivalent On-Resistance
- hFE Specified Up to 10A for a High Gain Hold Up
- Complementary PNP Type: FZT951
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The FZT851Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

- Case: SOT223 Type DN
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208<sup>(2)</sup>
- Weight: 0.112 grams (Approximate)



#### Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT851TA	AEC-Q101	FZT851	7	12	1000
FZT851QTA	Automotive	FZT851	7	12	1000

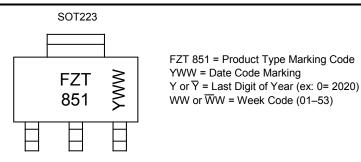
Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3).compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**





### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	150	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ic	6	А
Peak Pulse Current	I <sub>CM</sub>	20	А

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	6	3.0 24	W mW/°C	
Linear Derating Factor	(Note 6)	- P <sub>D</sub>	1.6 12.8		
Thermal Desistence, Junctice to Archiest	(Note 5)	R <sub>θJA</sub>	42		
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>θJA</sub>	78	°C/W	
Thermal Resistance Junction to Lead	(Note 7)	R <sub>eJL</sub>	8.8		
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

#### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

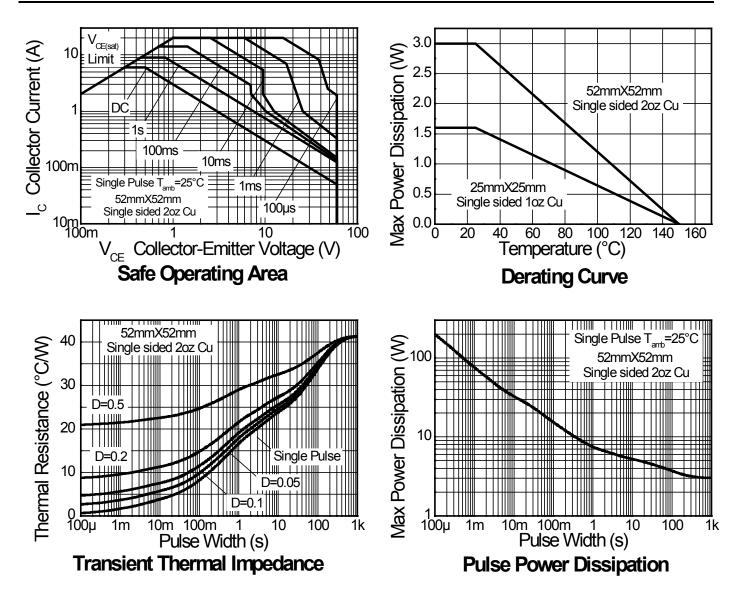
5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state. Notes:

6. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
7. Thermal resistance from junction to solder-point (at the end of the collector lead).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



# Thermal Characteristics and Derating Information





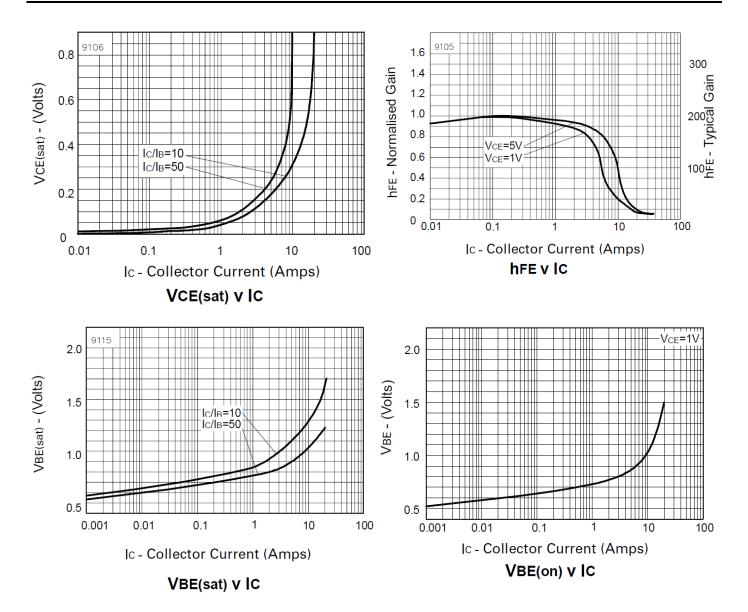
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	150	220	_	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	150	220	_	V	$I_{\rm C}$ = 1µA, R <sub>B</sub> ≤ 1kΩ
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	60	85	_	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.1	_	V	I <sub>E</sub> = 100μA
Collector Cut-Off Current	I <sub>CBO</sub>	-	<1 _	50 1	nΑ μΑ	V <sub>CB</sub> = 120V V <sub>CB</sub> = 120V, T <sub>A</sub> = +100°C
Collector Cut-Off Current	I <sub>CER</sub>	_	<1 —	50 1	nA µA	$V_{CE}$ = 120V, R <sub>B</sub> ≤ 1kΩ $V_{CE}$ = 120V, T <sub>A</sub> = +100°C
Emitter Cut-Off Current	I <sub>EBO</sub>	_	<1	10	nA	V <sub>EB</sub> = 6V
	h <sub>FE</sub>	100	200	_	_	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 1V
DC Current Cain (Note 0)		100	200	300		I <sub>C</sub> = 2A, V <sub>CE</sub> = 1V
DC Current Gain (Note 9)		75	120	—		I <sub>C</sub> = 5A, V <sub>CE</sub> = 1V
		25	50	—		I <sub>C</sub> = 10A, V <sub>CE</sub> = 1V
	V <sub>CE(sat)</sub>	_	—	50	mV	I <sub>C</sub> = 100mA, I <sub>B</sub> = 5mA
Collector Emitter Seturation Voltage (Note 0)			—	100		I <sub>C</sub> = 1A, I <sub>B</sub> = 50mA
Collector-Emitter Saturation Voltage (Note 9)			—	170		$I_{\rm C}$ = 2A, $I_{\rm B}$ = 50mA
		_	_	375		I <sub>C</sub> = 6A, I <sub>B</sub> = 300mA
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	_	_	1,200	mV	I <sub>C</sub> = 6A, I <sub>B</sub> = 300mA
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(on)</sub>	—		1,150	mV	I <sub>C</sub> = 6A, V <sub>CE</sub> = 1V
Current Gain-Bandwidth Product (Note 9)	ft	_	130	_	MHz	I <sub>C</sub> = 100mA, V <sub>CE</sub> = 10V, f = 50MHz
Output Capacitance	C <sub>obo</sub>	—	45	_	pF	V <sub>CB</sub> = 10V, f = 1MHz
Switching Times	t <sub>on</sub>	_	45	_	ne	$I_{\rm C}$ = 1A, $V_{\rm CC}$ = 10V,
	t <sub>off</sub>	_	1,100	_	ns	$I_{B1} = -I_{B2} = 100 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



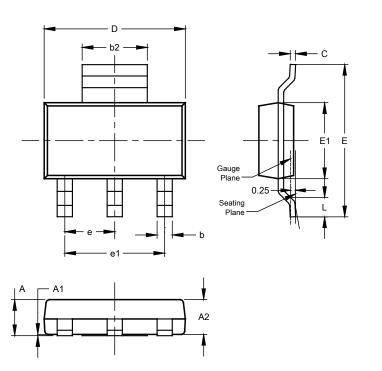
# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.



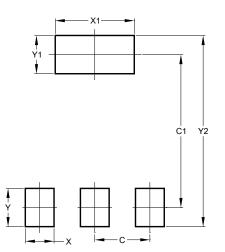
SC	SOT223 (Type DN)						
Dim	Min	Max	Тур				
Α		1.70	-				
A1	0.01	0.15	-				
A2	1.50	1.68	1.60				
b	0.60	0.80	0.70				
b2	2.90	3.10					
С	0.20	0.32					
D	6.30	6.70	-				
E	6.70	7.30					
E1	3.30	3.70	-				
е			2.30				
e1			4.60				
L	0.85						
All	All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)

SOT223 (Type DN)



Dimensions	Value (in mm)
	value (III IIIII)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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